

# DATA SHEET

**BUJ403A**

**Silicon Diffused Power Transistor**

Product specification

October 2018

## Silicon Diffused Power Transistor

BUJ403A

## GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

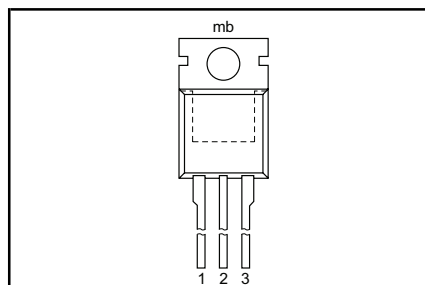
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0 \text{ V}$	-	1200	V
$V_{CBO}$	Collector-Base voltage (open emitter)		-	1200	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	550	V
$I_C$	Collector current (DC)		-	6	A
$I_{CM}$	Collector current peak value		-	10	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25 \text{ }^\circ\text{C}$	-	100	W
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 2 \text{ A}; I_B = 0.4 \text{ A}$	0.15	1.0	V
$h_{FEsat}$	DC current gain	$I_C = 3 \text{ A}; V_{CE} = 5 \text{ V}$	15.5	-	
$t_f$	Fall time	$I_C = 2.5 \text{ A}; I_{B1} = 0.5 \text{ A}$	170	300	ns

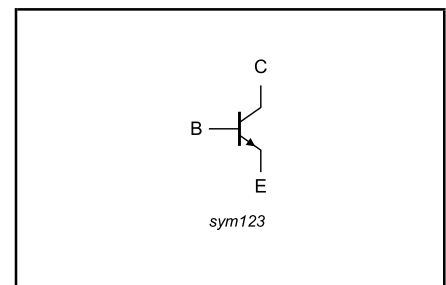
## PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector to emitter voltage	$V_{BE} = 0 \text{ V}$	-	1200	V
$V_{CEO}$	Collector to emitter voltage (open base)		-	550	V
$V_{CBO}$	Collector to base voltage (open emitter)		-	1200	V
$I_C$	Collector current (DC)		-	6	A
$I_{CM}$	Collector current peak value		-	10	A
$I_B$	Base current (DC)		-	3	A
$I_{BM}$	Base current peak value		-	5	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25 \text{ }^\circ\text{C}$	-	100	W
$T_{stg}$	Storage temperature		-65	150	$^\circ\text{C}$
$T_j$	Junction temperature		-	150	$^\circ\text{C}$

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base		-	1.25	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	60	-	K/W

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**STATIC CHARACTERISTICS** $T_{mb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}, I_{CBO}$ $I_{CES}$	Collector cut-off current <sup>1</sup>	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	1.0 2.0	mA mA
$I_{CEO}$ $I_{EBO}$ $V_{CEOsust}$	Collector cut-off current <sup>1</sup> Emitter cut-off current Collector-emitter sustaining voltage	$V_{CEO} = V_{CEOMmax}$ (550V) $V_{EB} = 7\text{ V}; I_C = 0\text{ A}$ $I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$	-	-	0.1 0.1 550	mA mA V
$V_{CEsat}$ $V_{BEsat}$	Collector-emitter saturation voltage Base-emitter saturation voltage	$I_C = 2.0\text{ A}; I_B = 0.4\text{ A}$ $I_C = 2.0\text{ A}; I_B = 0.4\text{ A}$	-	0.15 0.91	1.0 1.5	V V
$h_{FE}$	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$	13	25	-	-
$h_{FE}$	DC current gain	$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$	20	30	47	-
$h_{FEsat}$ $h_{FEsat}$	DC current gain	$I_C = 2.0\text{ A}; V_{CE} = 5\text{ V}$ $I_C = 3.0\text{ A}; V_{CE} = 5\text{ V}$	13	18.5 15.5	25 -	-

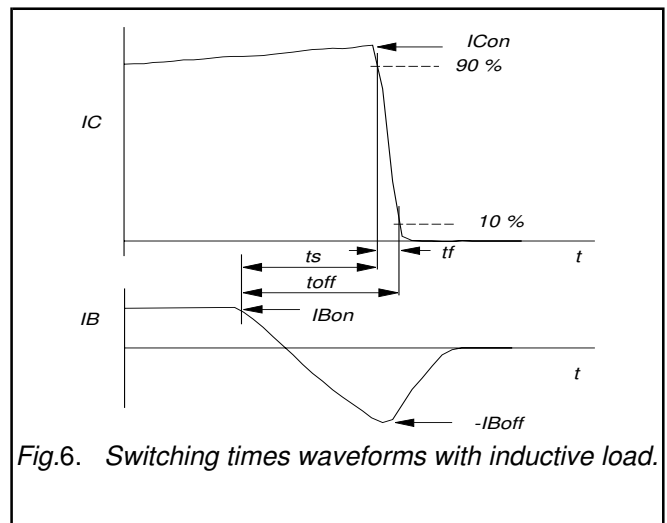
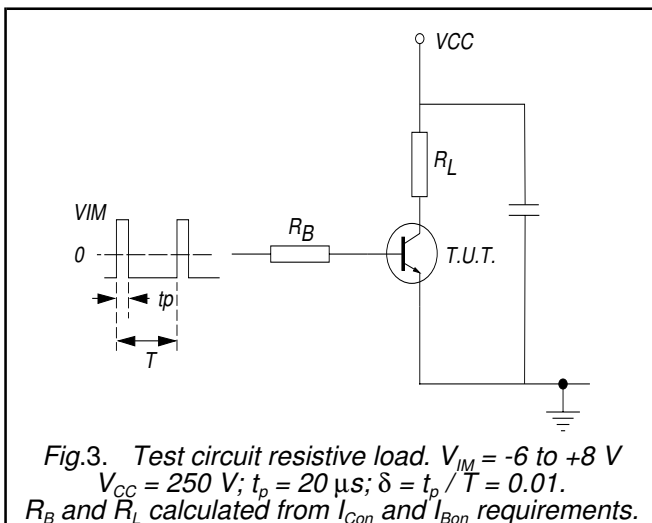
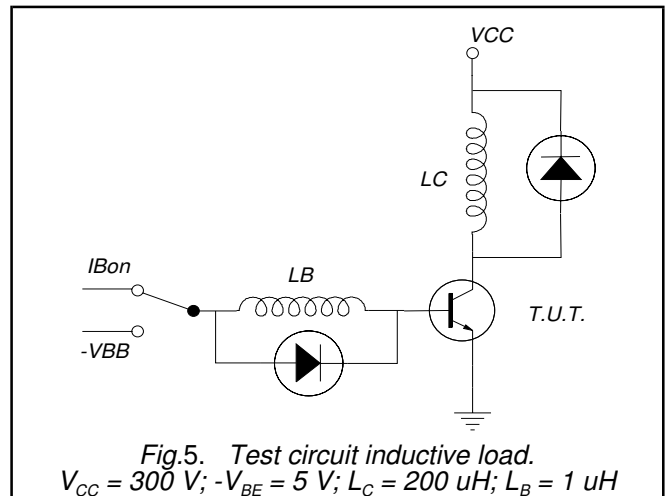
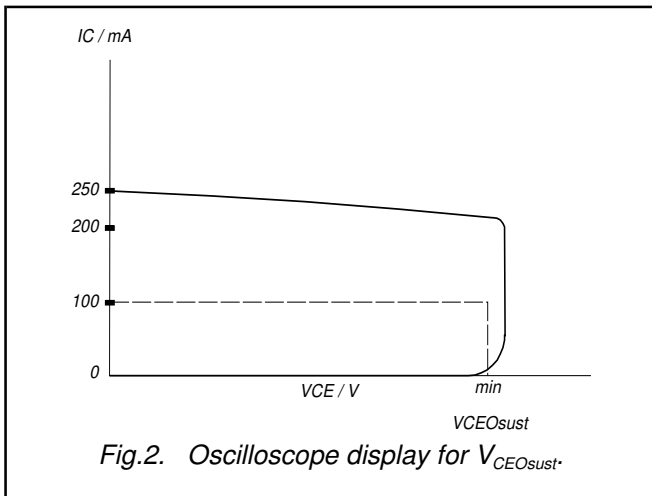
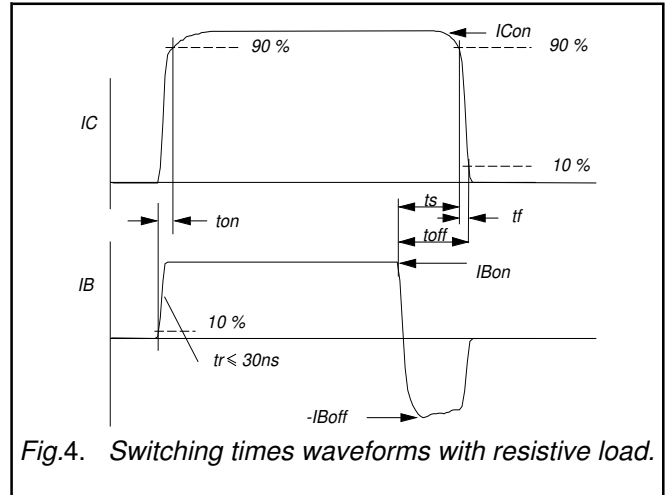
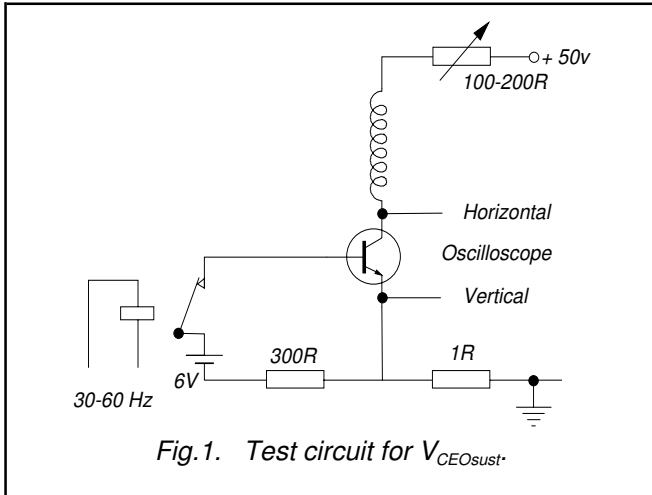
**DYNAMIC CHARACTERISTICS** $T_{mb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$t_{on}$ $t_s$ $t_f$	Switching times (resistive load) Turn-on time Turn-off storage time Turn-off fall time	$I_{Con} = 2.5\text{ A}; I_{Bon} = -I_{Boff} = 0.5\text{ A};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$	-	0.5 3 0.3	$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
$t_s$ $t_f$	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$	- 170	1.5 300	$\mu\text{s}$ ns
$t_s$ $t_f$	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 2.5\text{ A}; I_{Bon} = 0.5\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ }^{\circ}\text{C}$	-	1.8 300	$\mu\text{s}$ ns

<sup>1</sup> Measured with half sine-wave voltage (curve tracer).

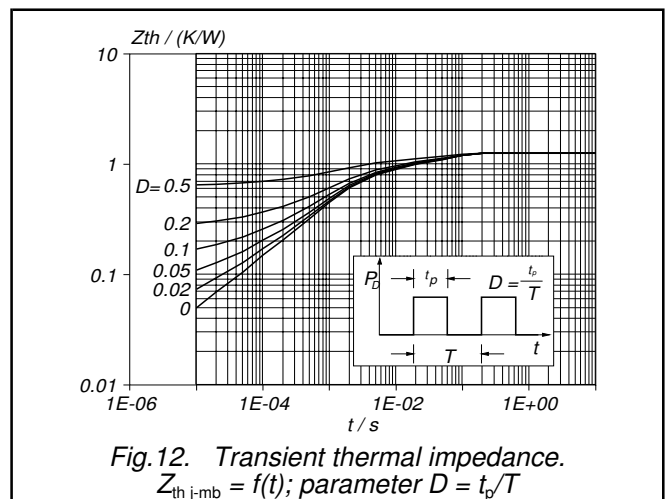
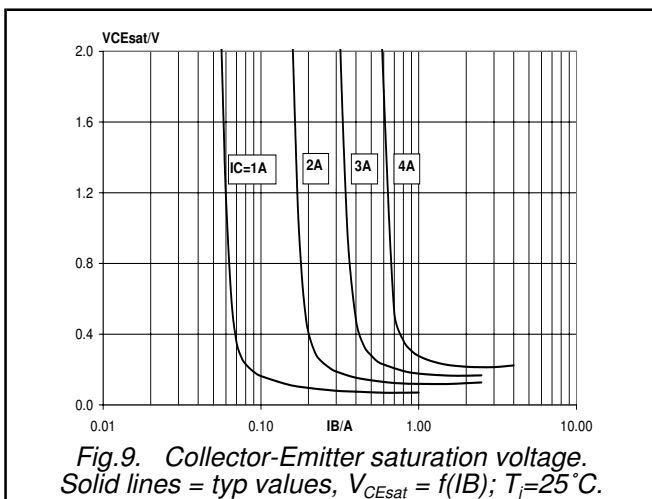
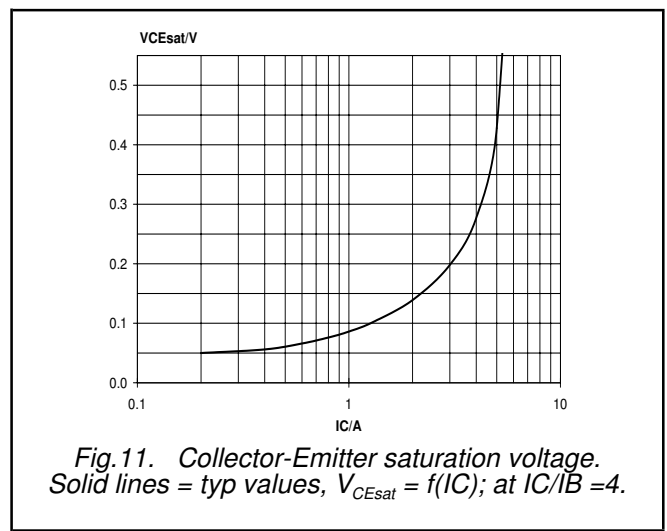
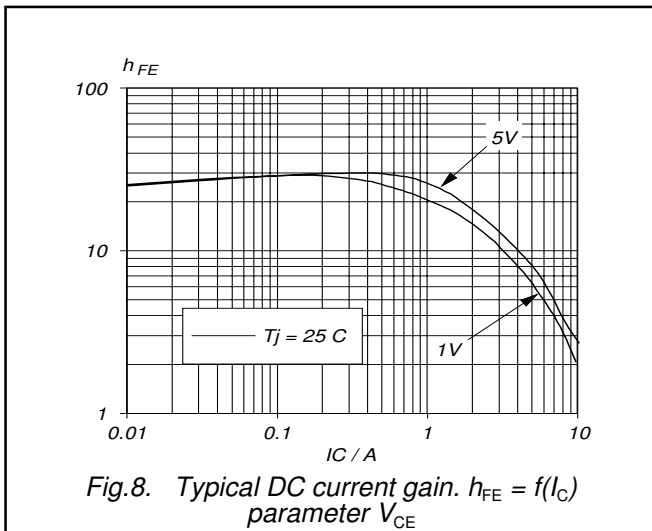
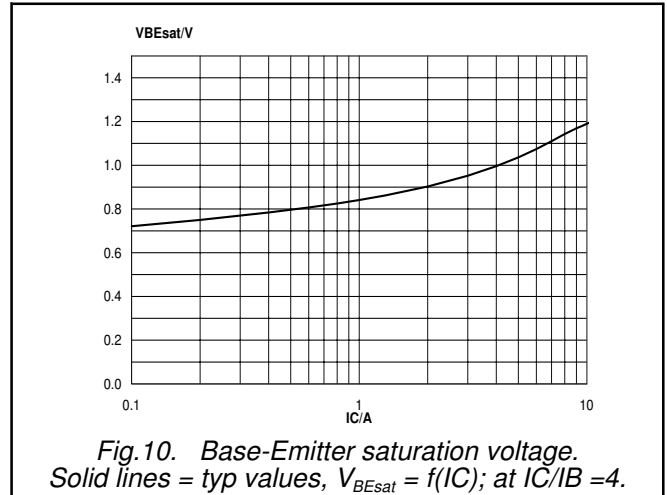
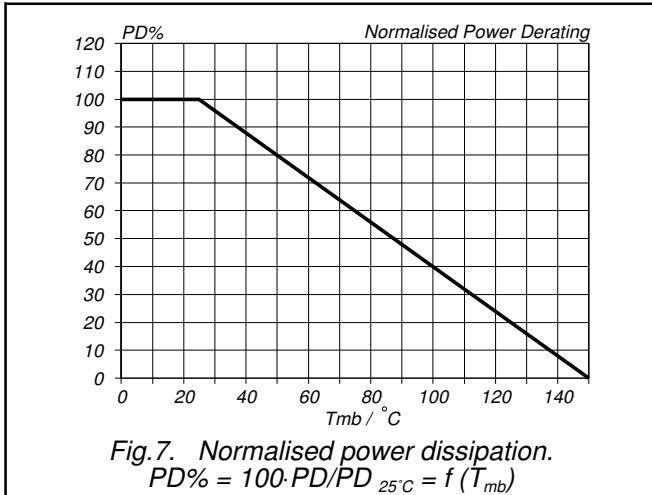
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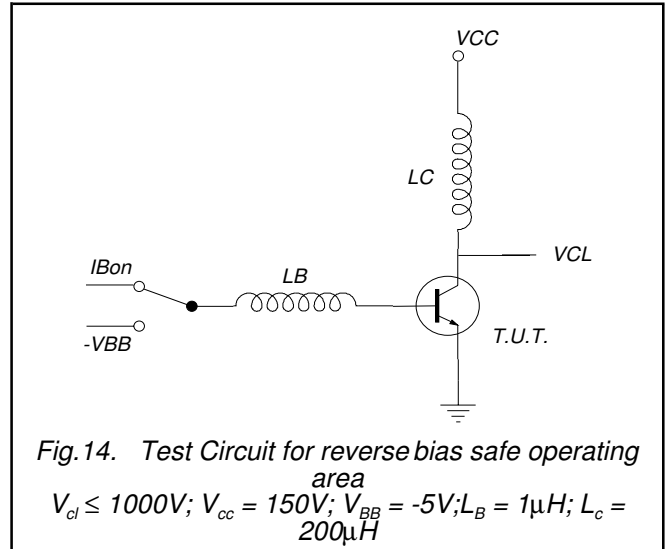
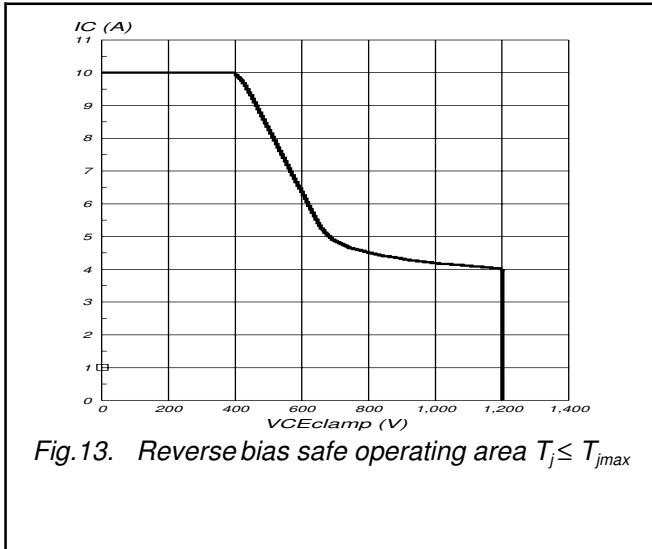
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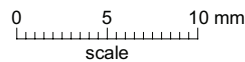
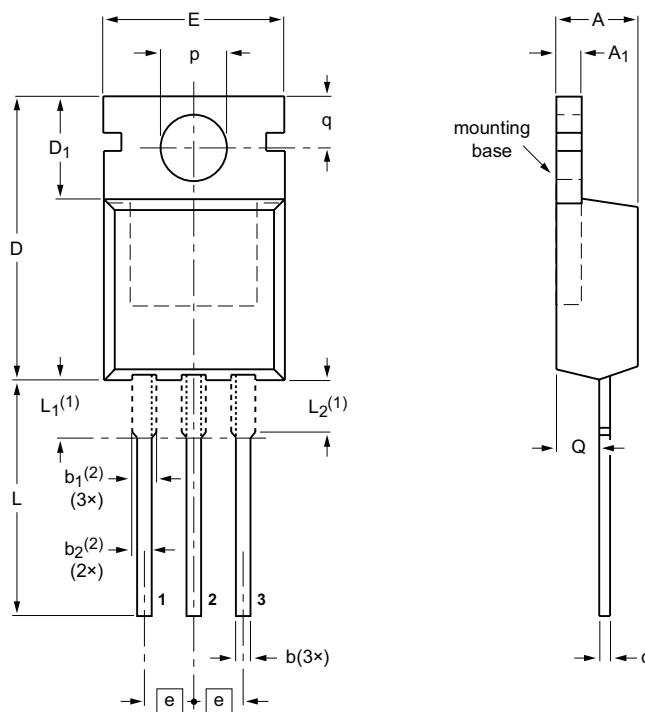
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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> (1)	L <sub>2</sub> (1) max.	p	q	Q
mm	4.7	1.40	0.9	1.6	1.3	0.7	16.0	6.6	10.3	2.54	15.0	3.30	3.0	3.8	3.0	2.6
	4.1	1.25	0.6	1.0	1.0	0.4	15.2	5.9	9.7		12.8	2.79		3.5	2.7	2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

## Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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